4V Drive Pch MOSFET

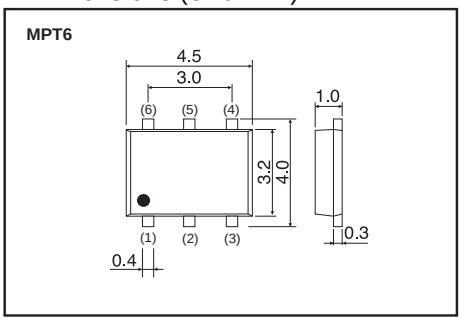
RP1E090RP

● Structure
Silicon P-channel MOSFET

● Features
1) Low on-resistance.
2) Built-in G-S Protection Diode.
3) Small Surface Mount Package (MPT6).

● Application
Switching

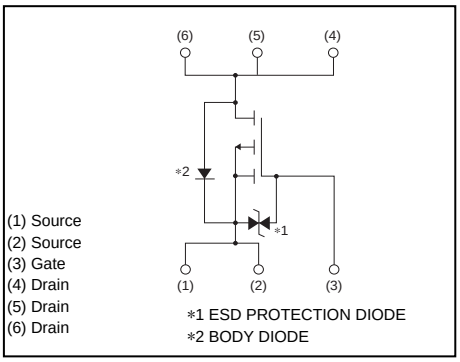
● Dimensions (Unit : mm)



● Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	1000
RP1E090RP		○

● Inner circuit



● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	−30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±9	A
	Pulsed	I_{DP} *1	±36	A
Source current (Body Diode)	Continuous	I_S	−1.6	A
	Pulsed	I_{SP} *1	−36	A
Power dissipation		P_D *2	2.0	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

*2 Mounted on a ceramic board.

● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	62.5	°C / W

*Mounted on a ceramic board.

● **Electrical characteristics** (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	−30	-	-	V	I_D=−1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	-	-	−1	μA	V_{DS}=−30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	−1.0	-	−2.5	V	V_{DS}=−10V, I_D=−1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	-	13	16.9	mΩ	I_D=−9A, V_{GS}=−10V
		-	18	25.2		I_D=−9A, V_{GS}=−4.5V
			21	29.4		I_D=−9A, V_{GS}=−4.0V
Forward transfer admittance	$\|Y_{fs}\|$*	10	-	-	S	I_D=−9A, V_{DS}=−10V
Input capacitance	C_{iss}	-	3000	-	pF	V_{DS}=−10V
Output capacitance	C_{oss}	-	360	-	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	-	360	-	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$*	-	20	-	ns	I_D=−4.5A, V_{DD}≒−15V
Rise time	t_r *	-	30	-	ns	V_{GS}=−10V
Turn-off delay time	$t_{d(off)}$*	-	135	-	ns	R_L=3.3Ω
Fall time	t_f *	-	80	-	ns	R_G=10Ω
Total gate charge	Q_g *	-	30	-	nC	I_D=−9A
Gate-source charge	Q_{gs} *	-	7	-	nC	V_{DD}≒−15V
Gate-drain charge	Q_{gd} *	-	11	-	nC	V_{GS}=−5V

*Pulsed

●**Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}*	-	-	−1.2	V	I_s=−9A, V_{GS}=0V

*Pulsed

● Electrical characteristic curves

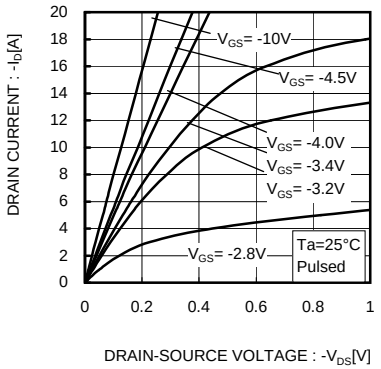


Fig.1 Typical output characteristics(Ⅰ)

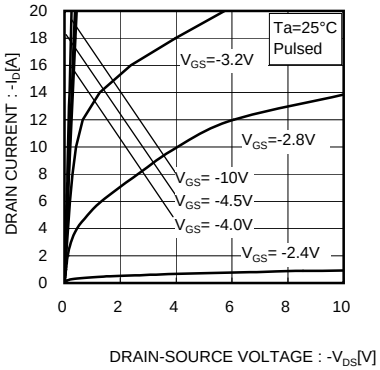


Fig.2 Typical output characteristics(Ⅱ)

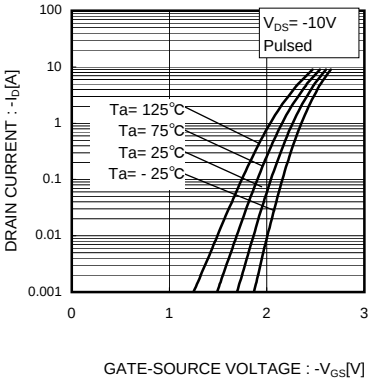


Fig.3 Typical Transfer Characteristics

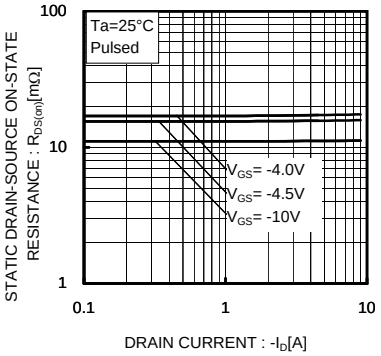


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(Ⅰ)

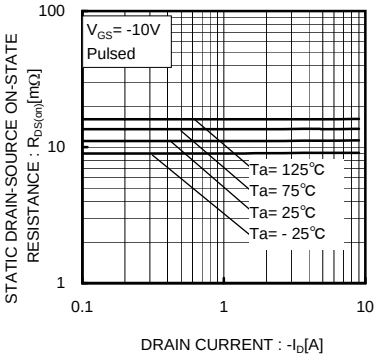


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(Ⅱ)

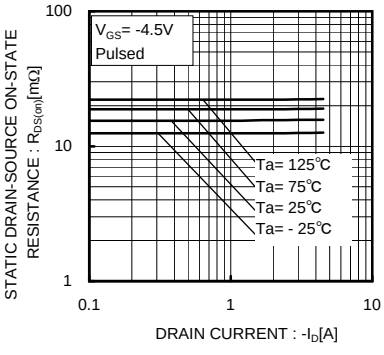


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

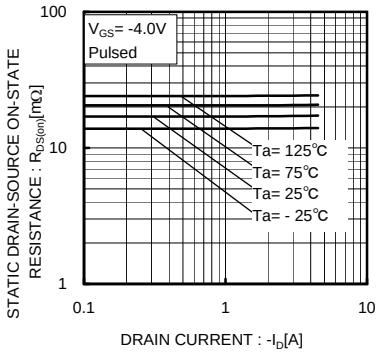


Fig.7 Static Drain-Source On-State Resistance vs. Drain

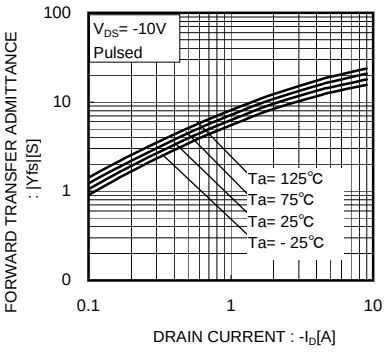


Fig.8 Forward Transfer Admittance vs. Drain Current

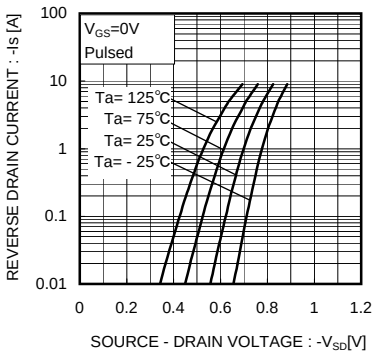


Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage

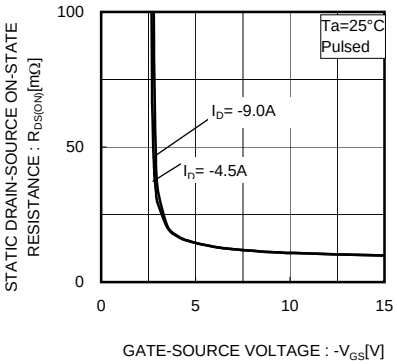


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

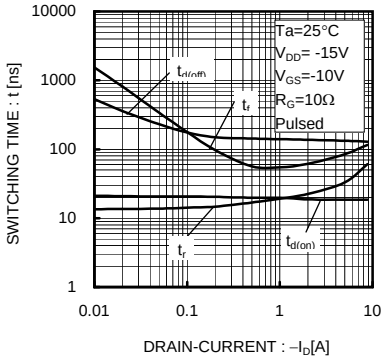


Fig.11 Switching Characteristics

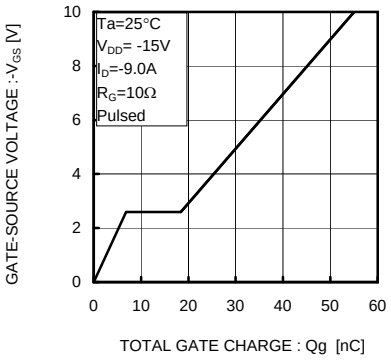


Fig.12 Dynamic Input Characteristics

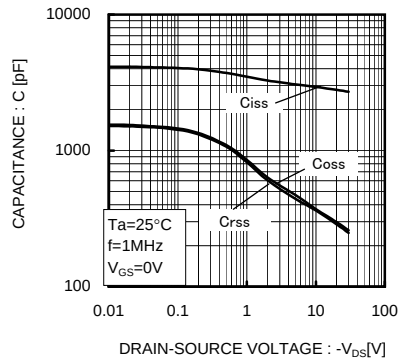


Fig.13 Typical Capacitance vs. Drain-Source Voltage

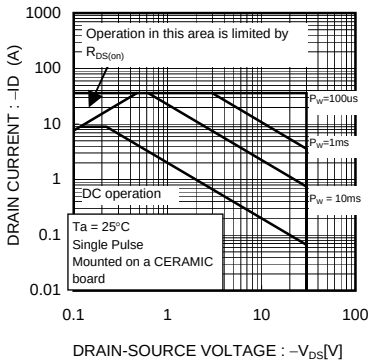


Fig.14 Maximum Safe Operating Aera

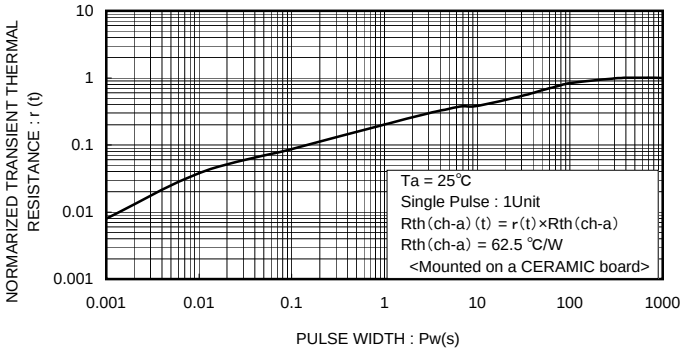


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

● Measurement circuits

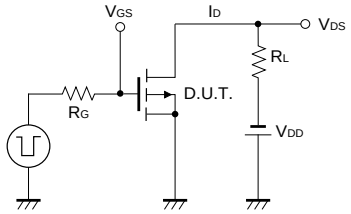


Fig.1-1 Switching Time Measurement Circuit

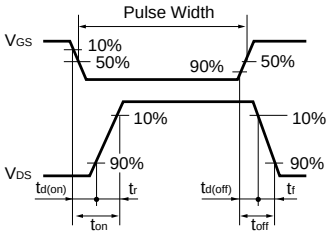


Fig.1-2 Switching Waveforms

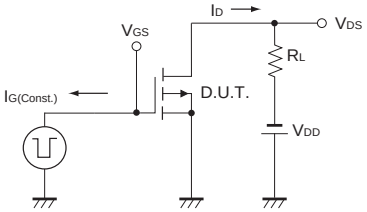


Fig.2-1 Gate charge measurement circuit

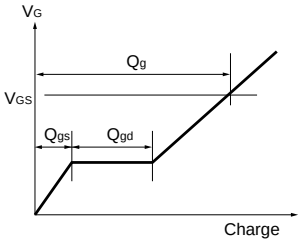


Fig.2-2 Gate Charge Waveform

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